



(51) International Patent Classification:

C01B 33/027 (2006.01) *C01B 33/035* (2006.01)
C01B 33/029 (2006.01) *C23C 16/01* (2006.01)
C01B 33/03 (2006.01) *C23C 16/24* (2006.01)

(21) International Application Number:

PCT/NO2012/050184

(22) International Filing Date:

25 September 2012 (25.09.2012)

(25) Filing Language:

Norwegian

(26) Publication Language:

English

(30) Priority Data:

20111304 26 September 2011 (26.09.2011) NO

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

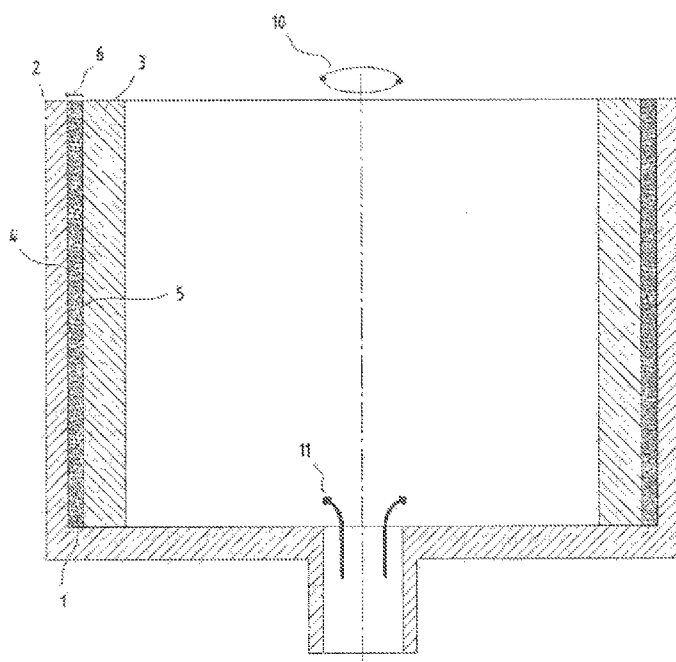
(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))

(54) Title: REACTOR AND METHOD FOR PRODUCTION OF SILICON BY CHEMICAL VAPOR DEPOSITION

FIG. 1



(57) Abstract: The invention provides a reactor for the manufacture of silicon by chemical vapour deposition (CVD), the reactor comprises a reactor body that can rotate around an axis with the help of a rotation device operatively arranged to the reactor, at least one sidewall that surrounds the reactor body, at least one inlet for reaction gas, at least one outlet for residual gas and at least one heat appliance operatively arranged to the reactor. The reactor is characterised in that during operation for the manufacture of silicon by CVD, the reactor comprises a layer of particles on the inside of, at least, one sidewall.